

# SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

# ECH8410-

# N-Channel Silicon MOSFET General-Purpose Switching Device Applications

# Features

- Low ON-resistance.
- 4V drive.
- Halogen free compliance.
- Protection diode in

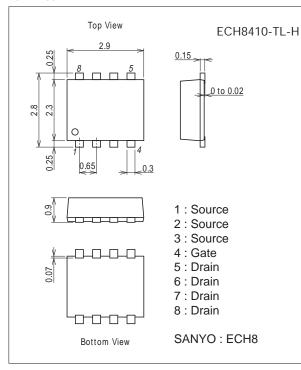
# **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		12	A
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	60	A
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Package Dimensions

unit : mm (typ.) 7011A-002

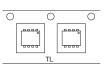


#### Product & Package Information

- Package : ECH8
- JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

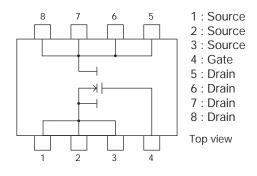
#### Packing Type : TL



# Marking



#### **Electrical Connection**

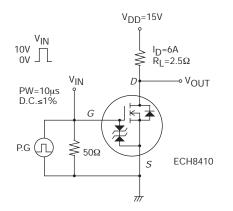


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## Electrical Characteristics at Ta=25°C

Parameter	Currents and	Conditions	Ratings			1114	
Parameter	Symbol	Conditions	min.	typ.	max.	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V	
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ	
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V	
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =6A		7.5		S	
	R <sub>DS</sub> (on)1	ID=6A, VGS=10V		7.5	10	mΩ	
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)2	ID=3A, VGS=4.5V		13	18.2	mΩ	
	R <sub>DS</sub> (on)3	ID=3A, VGS=4V		15.5	22	mΩ	
Input Capacitance	Ciss			1700		рF	
Output Capacitance	Coss	VDS=10V, f=1MHz		300		pF	
Reverse Transfer Capacitance	Crss			200		pF	
Turn-ON Delay Time	t <sub>d</sub> (on)			17		ns	
Rise Time	tr			50		ns	
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		110		ns	
Fall Time	tf	-		72		ns	
Total Gate Charge	Qg			31		nC	
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =12A		5.5		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		5.5		nC	
Diode Forward Voltage	V <sub>SD</sub>	IS=12A, VGS=0V		0.8	1.2	V	

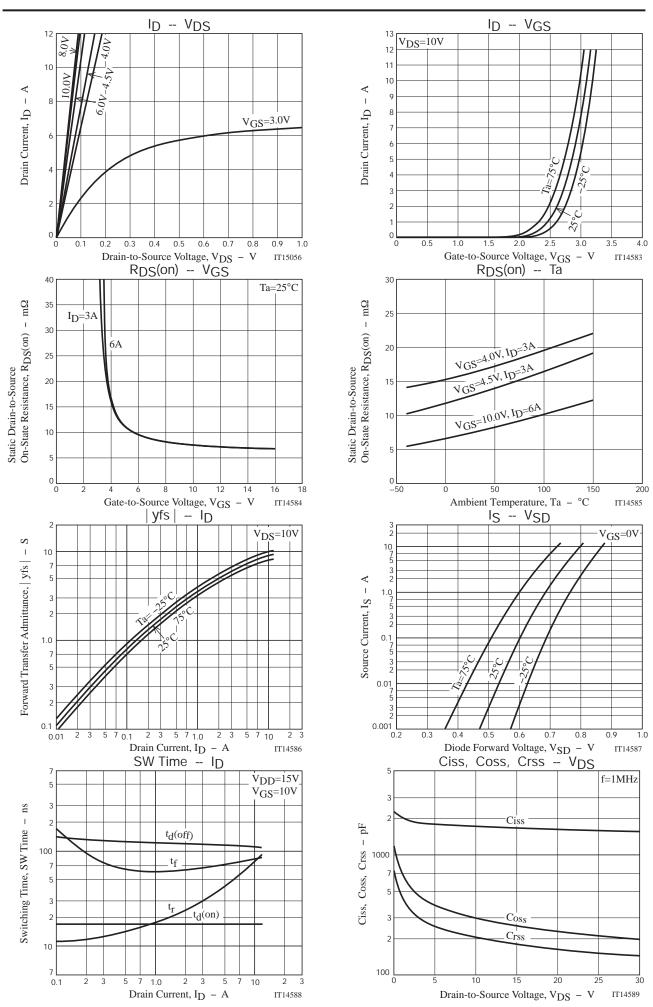
# Switching Time Test Circuit

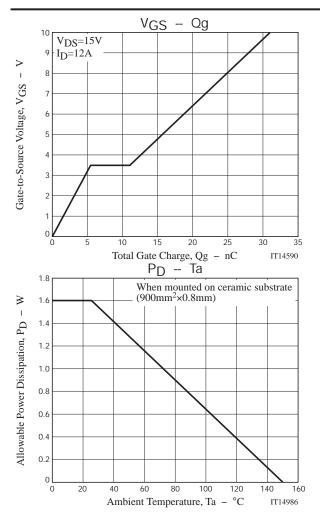


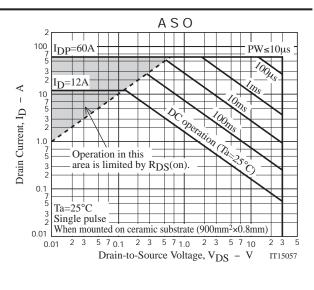
#### **Ordering Information**

Device Package		Shipping	memo	
ECH8410-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free	

## ECH8410







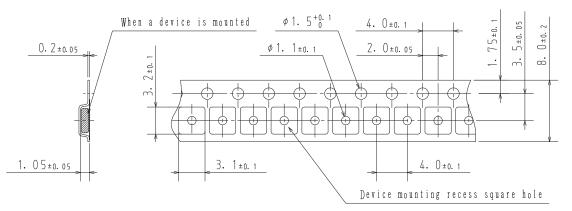
## Embossed Taping Specification ECH8410-TL-H

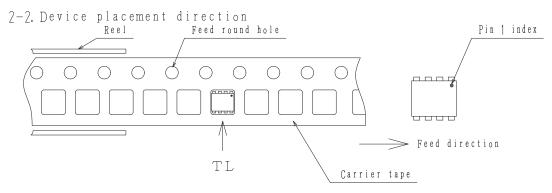
1. Packing Format

Package Name			ximum Number of ces contained (pcs)		Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1) Outer BOX (A-7)		
ECH8	CPH6	3,000	15,000	90,000	5 reels contained 6 inner boxes contained		
	_				Dimensions:mm (external) Dimensions:mm (external)		
					183×72×185 440×195×210		
<u>Reel label, Inner box label</u> (unit:mm) <u>Quter box label</u> (unit:mm) <u>Unit:mm</u> <u>Outer box label</u> [t is a label at the time of factory shipment: The form of a label may change in physical distribution process.							
	Type LOT Quan Orig	No. tity		TYPE   O   O   O     11 <td>000000 108   000000 ************************************</td>	000000 108   000000 ************************************		
Reel label The LEAD FREE * description shows that the surface treatment of the terminal is lead free.			of the terminal is lead free.				
				Label LEAD FRI LEAD FRI	CE 3 JEITA Phase 3A		

2. Taping configuration

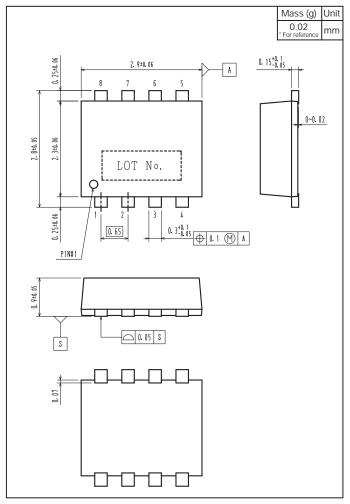
2-1. Carrier tape size (unit:mm)



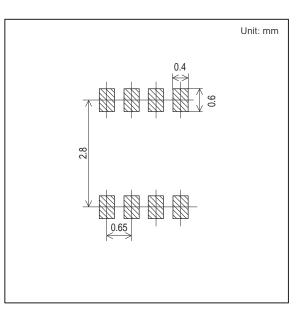


Those with pin 1 index on the feed hole side·····TL

# Outline Drawing ECH8410-TL-H



Land Pattern Example



Note on usage : Since the ECH8410 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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